

*Amended
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layer on said group-III nitride crystal layer, wherein at least a second conduction-type surface ohmic electrode conductive with said window layer is between the surface of said group-III nitride crystal layer and said window layer and comes into contact with the surface of said group-III nitride crystal layer and is disposed in an open light-emitting region other than a projective region of a pad electrode on the surface of said group-III nitride crystal layer, the pad electrode for wire bonding is on the center of the upper surface of said window layer, and wherein a sum of areas of said second conduction-type surface ohmic electrodes is from 5 to 30% of a total area of said open light-emitting region.

22. (Amended) An electrode for group-III nitride semiconductor light-emitting diodes for a group-III nitride semiconductor light-emitting diode comprising at least a gallium nitride (GaN)-based group-III nitride crystal layer having a light-emitting part of a hetero-junction structure, and a window layer comprising an electrically conducting transparent oxide crystal layer provided on said group-III nitride crystal layer, wherein at least a surface ohmic electrode conductive with said window layer is between the surface of said group-III nitride crystal layer and said window layer and is disposed in an open light-emitting region other than a projective region of a pad electrode on the surface of said group-III nitride crystal layer and comes into contact with the surface of said group-III nitride crystal layer, and said pad electrode for wire bonding is on the center of the upper surface of said window layer, wherein a sum of areas of said surface ohmic electrodes is from 5 to 30% of a total area of the open light-emitting region.